

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	2	("6545335").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/08/18 10:18
S2	2	("4801993").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/08/18 10:23
S3	2	("5311046").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/08/18 10:23
S4	2	("5726462").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/08/18 10:24
S5	2	("5978408").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/08/18 10:28
S6	2	("5985687").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/08/18 10:25
S7	1286	(372/96).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/08/18 10:28
S8	1056	(372/96).CCLS.	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/08/18 10:29

S9	802	372/96.ccls. and (oxide or insulat\$3 or dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/08/18 10:30
S10	42	(optoelectronic or (light adj (emit\$3 or detect\$3))) and ((dielectric or insulat\$3 or oxide) with (second adj component))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/19 11:59
S11	27	(optoelectronic or (light adj (emit\$3 or detect\$3))) and ((dielectric or insulat\$3 or oxide) with (second adj component))	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/08/17 15:39
S12	21	(optoelectronic or (light adj (emit\$3 or detect\$3))) and ((dielectric or insulat\$3 or oxide) with (second adj device))	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/08/17 16:11
S13	445	(optoelectronic or (light adj (emit\$3 or detect\$3))) and ((dielectric or insulat\$3 or oxide) with (second adj layer))	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/08/18 10:16
S14	77	opto\$1electronic and (oxidize\$3 with (cavity or hole or groove))	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/24 14:13
S15	5	opto\$1electronic and (lateral near oxidize\$3)	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/24 15:25
S16	211	438/362	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/24 15:32
S17	172	(lateral\$4 near oxidiz\$4)	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/24 15:42
S18	81	(lateral\$4 with oxidiz\$4 with (hole or groove or cavity))	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/24 17:05
S19	1327	(transistor with photo\$1detector)	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/24 17:44
S20	2	("6329699").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/24 17:44

S21	2	("5925975").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/24 17:45
S22	2	("5702281").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/24 17:45
S23	2	("6284581").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/24 17:46
S24	2	("6433428").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/25 10:32
S25	1198	(257/79).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/25 10:35
S26	614	(257/88).CCLS.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/25 10:35
S27	2	("6148016").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/18 15:00
S28	2	("5457061").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/19 13:33
S29	16269	"257"/\$.ccls. and (oxide with gate with deposit\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/19 13:34
S31	3035	"257"/\$.ccls. and (oxide with gate with deposit\$4 with (gate adj electrode))	USPAT	OR	OFF	2005/11/19 13:37
S32	1268	"257"/\$.ccls. and (oxide with gate with deposit\$4 with (gate adj electrode)) and memory	USPAT	OR	OFF	2005/11/19 15:21

S33	256	"257"/\$.ccls. and (oxide with gate with deposit\$4 with (gate adj electrode)) and (control adj gate) and (floating adj gate)	USPAT	OR	OFF	2005/11/19 14:41
S34	93	"257"/\$.ccls. and (oxide with gate with deposit\$4 near3 (gate adj electrode)) and (control adj gate) and (floating adj gate)	USPAT	OR	OFF	2005/11/19 13:41
S35	162	"438"/\$.ccls. and (oxide with gate with deposit\$4 with (gate adj electrode)) and (control adj gate) and (floating adj gate)	USPAT	OR	OFF	2005/11/19 14:41
S36	264	"438"/\$.ccls. and (oxide with gate with deposit\$4 with (gate adj electrode)) and (control adj gate) and (floating adj gate)	US-PGPUB; USPAT	OR	OFF	2005/11/19 14:41
S37	1782	"257"/\$.ccls. and (oxide with gate with deposit\$4 with (gate adj electrode)) and memory	US-PGPUB; USPAT	OR	OFF	2005/11/19 15:42
S38	98	"257"/\$.ccls. and (oxide with (top near2 gate) with deposit\$4 with (gate adj electrode))	US-PGPUB; USPAT	OR	OFF	2005/11/21 11:13
S39	2	("6762480").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/21 11:49
S40	2	("6399971").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/21 11:14
S41	104	"257"/\$.ccls. and (base) and (collector) and (emitter) and (Ga\$4As\$4Sb\$4) or (As\$4Ga\$4Sb\$4) or (Sb\$4As\$4Ga\$4) or (Sb\$4Ga\$4As\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/21 11:52
S42	104	"257"/\$.ccls. and (base) and (collector) and (emitter) and (Ga\$4As\$4Sb\$4) or (As\$4Ga\$4Sb\$4) or (Sb\$4As\$4Ga\$4) or (Sb\$4Ga\$4As\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/21 15:29
S43	98	"257"/\$.ccls. and (base) and (collector) and (emitter) and (Ga\$4As\$4Sb\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/21 13:17

S44	29	"257"/\$.ccls. and (base) and (emitter) and (Ga\$10Sb\$10As or As\$10Sb\$10Ga\$10)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/21 15:10
S45	44	"257"/\$.ccls. and (base) and (emitter) and (Ga\$10Sb\$10As\$10 or As\$10Sb\$10Ga\$10)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/21 15:10
S46	40	"438"/\$.ccls. and (base) and (collector) and (emitter) and (Ga\$4As\$4Sb\$4) or (As\$4Ga\$4Sb\$4) or (Sb\$4As\$4Ga\$4) or (Sb\$4Ga\$4As\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/21 15:22
S47	23	"257"/\$.ccls. and (base) and (emitter) and (gallium adj arsenide adj antimonide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/21 15:38
S48	8	(base) and (emitter) and (gallium adj arsenide adj antimonide).clm.	US-PGPUB	OR	OFF	2005/11/21 15:38
S49	37	(base) and (emitter) and ((gallium adj arsenide adj antimonide) or (Ga\$8As\$8Sb\$8)).clm.	US-PGPUB	OR	OFF	2005/11/21 15:39
S50	37	(base) and (emitter) and ((gallium adj arsenide adj antimonide) or (Ga\$8As\$8Sb\$8) or (Sb\$8Ga\$8As\$8)).clm.	US-PGPUB	OR	OFF	2005/11/21 16:07
S51	2250	(257/197-198,592).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/21 16:14
S52	1987	(257/197-198,592).CCLS.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/21 16:14